

60 V, single N-channel Trench MOSFET Rev. 2 — 13 June 2012

Product data sheet

1. **Product profile**

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV

1.3 Applications

- Relay driver
- High-speed line driver

1.4 Quick reference data

- Logic-level compatible
- Ultra thin package profile with 0.37 mm height
- Low-side loadswitch
- Switching circuits

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C	<u>[1]</u>	-	-	450	mA
Static cha	aracteristics						
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 450 mA; T _j = 25 °C		-	1	1.6	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		2
2	S	source		D
3	D	drain	2 Transparent top view SOT883B (DFN1006B-3)	G S 017aaa255

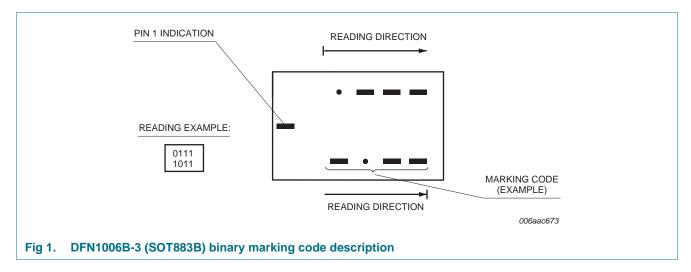
3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
2N7002BKMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B		

4. Marking

Table 4. Marking codes

Type number	Marking code
2N7002BKMB	0000 0001



2N7002BKMB

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5. Limiting values

Table 5. Limiting values

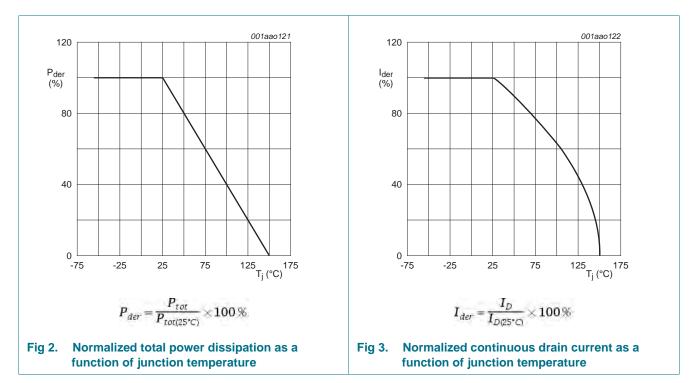
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	<u>[1]</u>	-	450	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	<u>[1]</u>	-	220	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	1.8	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	2700	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	450	mA
ESD maxim	um rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

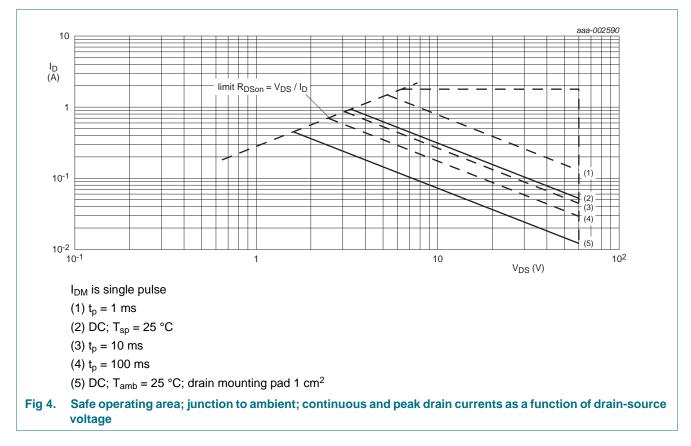
[3] Measured between all pins.



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6. Thermal characteristics

Table 6.	Thermal characteristics	

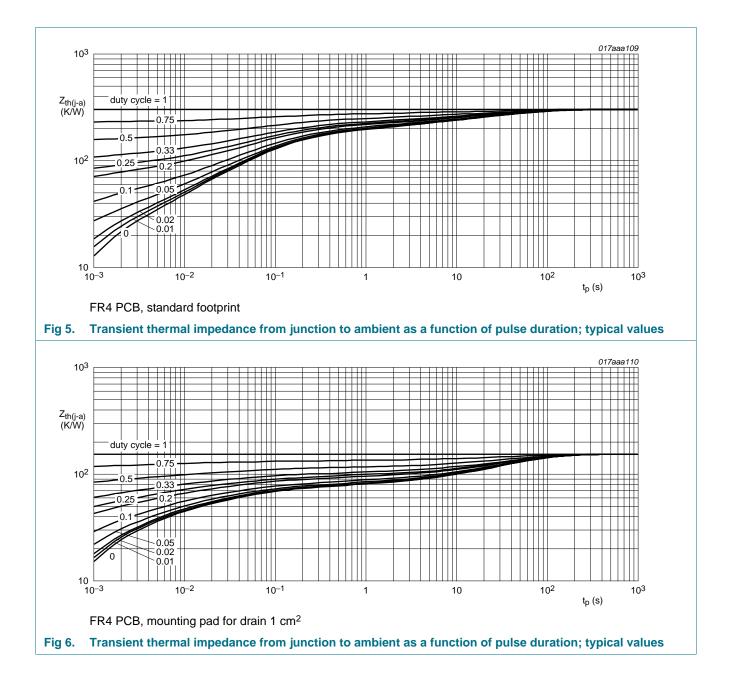
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	<u>[1]</u>	-	305	350	K/W
	from junction to ambient		<u>[2]</u>	-	150	175	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	40	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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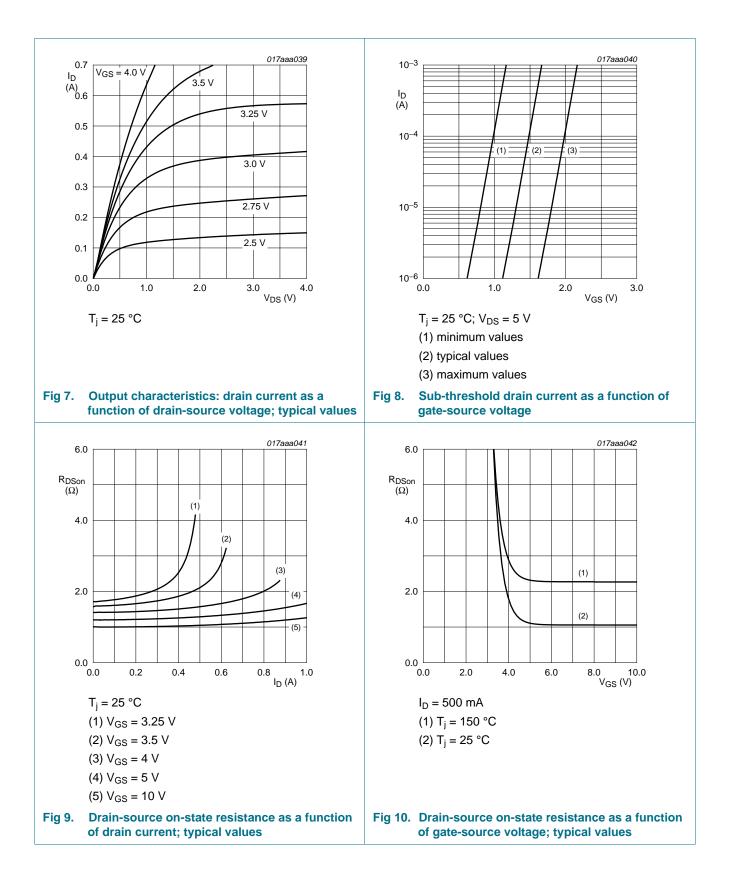
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7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 10 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	60	-	-	V
V _{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; \text{ V}_{DS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	-	10	μΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	10	μA
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I _D = 450 mA; T _j = 25 °C	-	1	1.6	Ω
resis	resistance	V_{GS} = 10 V; I _D = 450 mA; T _j = 150 °C	-	2.2	3.5	Ω
		$V_{GS} = 5 \text{ V}; \text{ I}_{D} = 50 \text{ mA}; \text{ T}_{j} = 25 \text{ °C}$	-	1.3	2	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 200 mA; T_{j} = 25 °C	-	550	-	mS
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 30 V; I_{D} = 300 mA; V_{GS} = 4.5 V;	-	0.5	0.6	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.2	-	nC
Q _{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V_{DS} = 10 V; f = 1 MHz; V_{GS} = 0 V;	-	33	50	pF
C _{oss}	output capacitance	T _j = 25 °C	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 50 V; R_L = 250 Ω ; V_{GS} = 10 V;	-	5	10	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	6	-	ns
t _{d(off)}	turn-off delay time		-	12	24	ns
t _f	fall time		-	7	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _i = 25 °C	0.47	0.75	1.1	V

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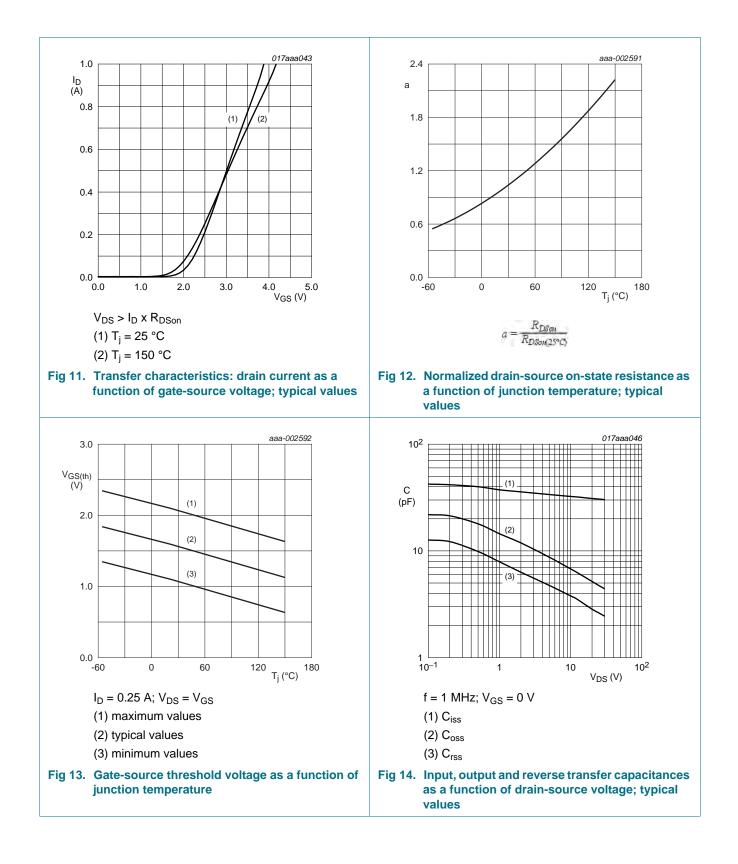
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Product data sheet

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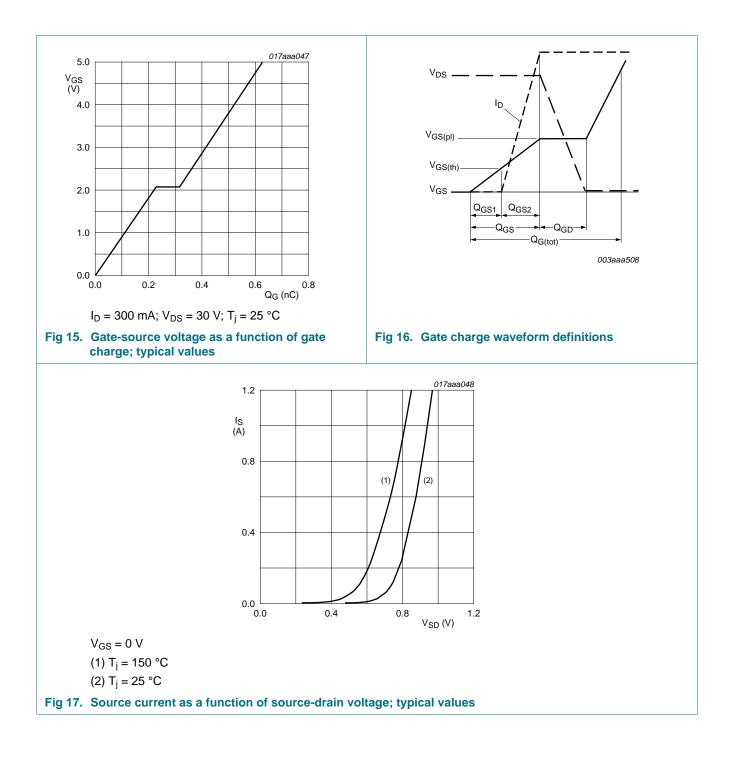
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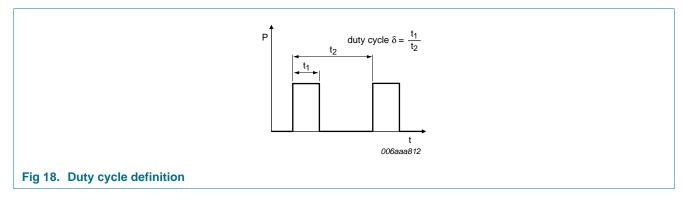
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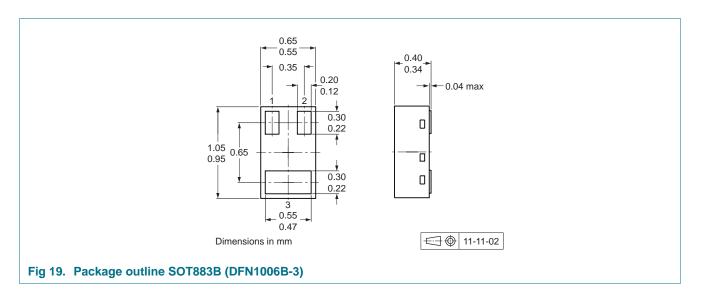


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8. Test information



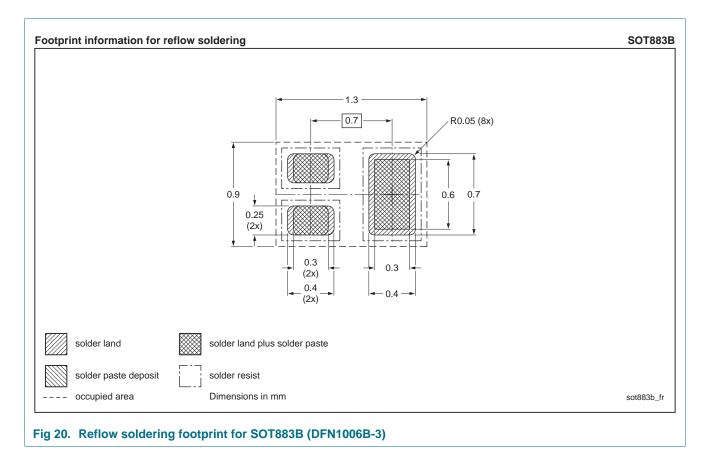
9. Package outline



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10. Soldering



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11. Revision history

Table 8.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
2N7002BKMB v.2	20120613	Product data sheet	-	2N7002BKMB v.1
Modifications:	• 7 "Characteris	stics": R _{DSon} condition corre	cted	
2N7002BKMB v.1	20120511	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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